imall

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DUAL 20V NPN LOW SATURATION SWITCHING TRANSISTOR

Features and Benefits

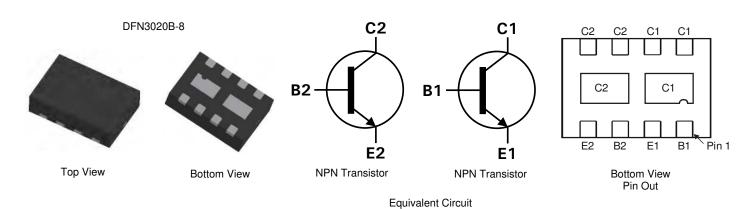
- $BV_{CEO} > 20V$
- I_C = 4.5A Continuous Collector Current
- Low Saturation Voltage (150mV @ 1A)
- $R_{SAT} = 47m\Omega$ for a Low Equivalent On-Resistance
- hFE specified up to 6A for high current gain hold up
- Dual NPN saving footprint and component count
- Low profile 0.8mm high package for thin applications .
- ReJA efficient, 40% lower than SOT26
- 6mm² footprint, 50% smaller than TSOP6 and SOT26 .
- Lead-Free, RoHS Compliant (Note 1) .
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: DFN3020B-3
- Case material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- UL Flammability Rating 94V-0
- Nominal package height: 0.8mm
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.013 grams (approximate)

Applications

- **DC-DC Converters**
- Charging circuits
- Motor control
- Power switches
- Portable applications



Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD618MCTA	DBB	7	8	3,000

Notes: 1. No purposefully added lead.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

3. For Packaging Details, go to our website at http://www.diodes.com.

Marking Information



DBB = Product Type Marking Code Top View, Dot Denotes Pin 1



Maximum Ratings @T_A = 25°C unless otherwise specified

Parameter	Symbol	Limit	Unit	
Collector-Base Voltage	V _{CBO}	40		
Collector-Emitter Voltage	V _{CEO}	20	V	
Emitter-Base Voltage	V _{EBO}	7		
Peak Pulse Current	I _{CM}	12		
Continuous Collector Current (Notes 4 and 7)	Ic	4.5	•	
Continuous Collector Current (Notes 5 and 7)	I _C	5		
Base Current	IB	1		

Thermal Characteristics @ TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit	
	(Notes 4 & 7)		1.5 12		
Power Dissipation	(Notes 5 & 7)		2.45 19.6	w	
Linear Derating Factor	(Notes 6 & 7)	PD	1.13 8	mW/°C	
	(Notes 6 & 8)		1.7 13.6		
	(Notes 4 & 7)		83.3		
Thermal Desistance, lumetica to Archient	(Notes 5 & 7)		51.0		
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	R _{0JA}	111	°C/W	
	(Notes 6 & 8)		73.5		
Thermal Resistance, Junction to Lead	(Notes 7 & 9)	R _{θJL}	17.1		
Operating and Storage Temperature Range	•	T _J , T _{STG}	-55 to +150	°C	

Notes: 4. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.

Same as note (4), except the device is measured at t <5 sec.
 Same as note (4), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.

7. For a dual device with one active die.

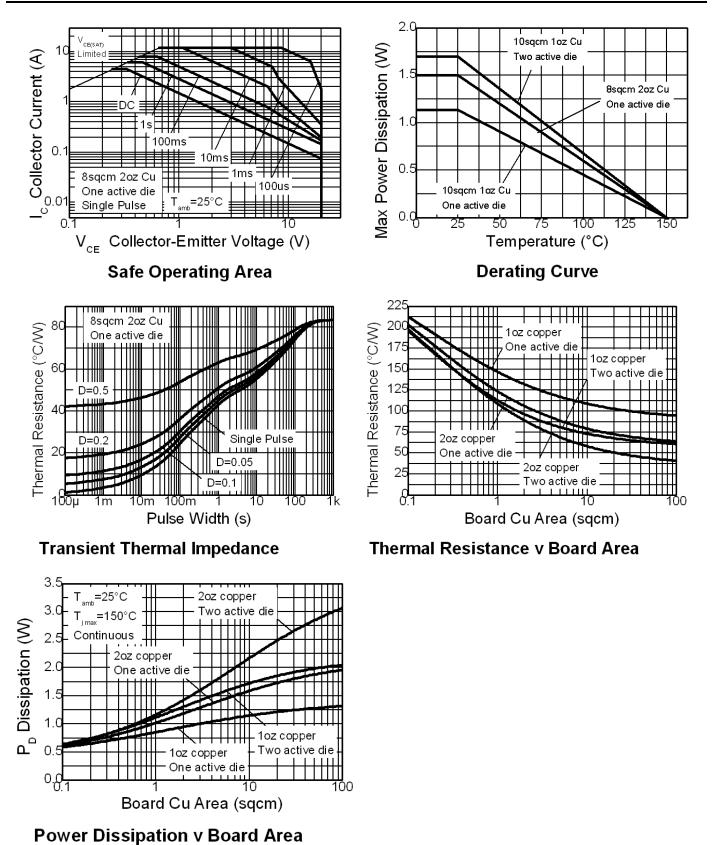
8. For dual device with 2 active die running at equal power.

9. Thermal resistance from junction to solder-point (at the end of the collector lead).





Thermal Characteristics





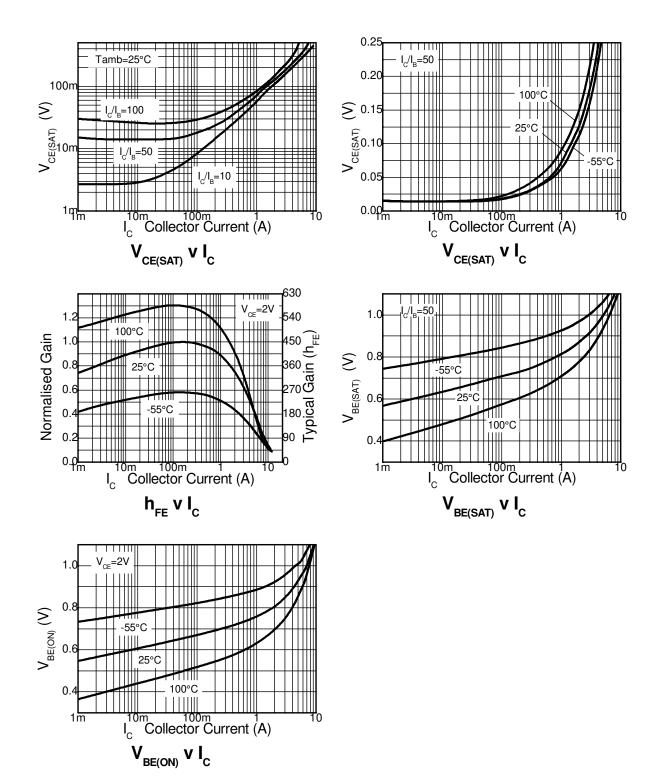
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	100	-	V	$I_{\rm C} = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	20	27	-	V	$I_{\rm C} = 10 {\rm mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7.0	8.2	-	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	-	100	nA	V _{CB} = 30V
Emitter Cutoff Current	I _{EBO}	-	-	100	_ nA	$V_{EB} = 6V$
Collector Emitter Cutoff Current	ICES	-	-	100	nA	$V_{CES} = 16V$
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	200 300 200 100	400 450 360 180		-	$I_{C} = 10mA, V_{CE} = 2V$ $I_{C} = 200mA, V_{CE} = 2V$ $I_{C} = 2A, V_{CE} = 2V$ $I_{C} = 6A, V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}		8 90 115 190 210	15 150 135 250 300	mV	$\begin{split} I_{C} &= 0.1A, \ I_{B} = 10 mA \\ I_{C} &= 1A, \ I_{B} = 10 mA \\ I_{C} &= 2A, \ I_{B} = 50 mA \\ I_{C} &= 3A, \ I_{B} = 100 mA \\ I_{C} &= 4.5A, \ I_{B} = 125 mA \end{split}$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	-	0.88	0.97	V	$I_{C} = 4.5A, V_{CE} = 2V$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	0.98	1.07	V	I _C = 4.5A, I _B = 125mA
Output Capacitance	C _{obo}	-	23	30	pF	V _{CB} = 10V. f = 1MHz
Transition Frequency	f _T	100	140	-	MHz	$V_{CE} = 10V, I_C = 50mA, f = 100MHz$
Turn-on Time	t _{on}	-	170	-	ns	$V_{CC} = 10V, I_{C} = 3A$
Turn-off Time	t _{off}	-	400	-	ns	$I_{B1} = I_{B2} = 10 \text{mA}$

Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 µs. Duty cycle \leq 2%



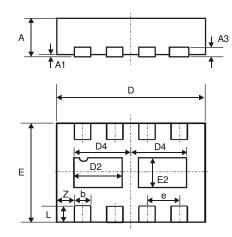
Typical Electrical Characteristics





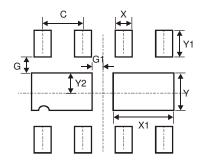


Package Outline Dimensions



DFN3020B-8					
Dim	Min	Max	Тур		
Α	0.77	0.83	0.80		
A1	0	0.05	0.02		
A3	-	-	0.15		
b	0.25	0.35	0.30		
D	2.95	3.075	3.00		
D2	0.82	1.02	0.92		
D4	1.01	1.21	1.11		
е	-	-	0.65		
Е	1.95	2.075	2.00		
E2	0.43	0.63	0.53		
L	0.25	0.35	0.30		
Ζ	-	-	0.375		
All I	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)			
С	0.650			
G	0.285			
G1	0.090			
Х	0.400			
X1	1.120			
Y	0.730			
Y1	0.500			
Y2	0.365			



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